

ABSTRACT OF THE DISCLOSURE

Reaction products produced under dry etching attach to a substrate undergoing dry etching. It is necessary to remove the reaction products for the next step. Therefore, in the case of the background art, the processing of supplying a remover for
5 reaction products, an intermediate rinse for washing away the remover, and deionized water to a substrate in order is performed.

The above processing is conventionally performed under an atmospheric atmosphere. Therefore, a thin film may be changed in quality due to atmospheric components.

10 Therefore, a substrate processing apparatus of the present invention uses means for blowing nitrogen gas on a substrate and supplies a remover to the substrate while blowing nitrogen. Thereby, it is possible to prevent a thin film from being changed in quality due to atmospheric components.